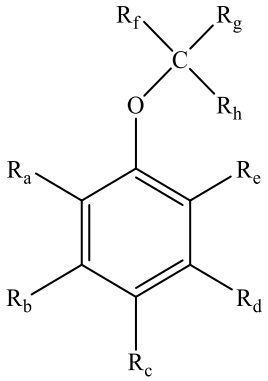
What is claimed is:

1. A rinse comprising

(i) between 15% by weight and 35% by weight of acetic acid and

(ii) between 85% by weight and 65% by weight of a compound having structure B:



wherein each of R_a, R_b, R_c, R_d, R_e, R_f, R_g and R_h may independently be hydrogen, a substituted or an unsubstituted (C_{1-6}) alkyl group, a substituted or an unsubstituted halogenated (C_{1-6}) alkyl group, a substituted or an unsubstituted (C_{1-6}) alkyl carbonyl group, a halogen, or a hydroxy group.

2. The rinse of claim 1, wherein each of R_a, R_b, R_c, R_d, R_e, R_f, R_g and R_h in structure B is hydrogen.

3. The rinse of claim 1, wherein the rinse contains 15% by weight of acetic acid.

4. The rinse of claim 1, wherein the rinse contains 20% by weight of acetic acid.

5. The rinse of claim 1, wherein the rinse contains 25% by weight of acetic acid.

6. The rinse of claim 1, wherein the rinse contains 30% by weight of acetic acid.

7. The rinse of claim 1, wherein the rinse contains 35% by weight of acetic acid.

8. A method of cleaning a wafer or substrate comprising:

washing the wafer or substrate with a rinse according to claim 1.

9. The method of claim 8, wherein each of R_a, R_b, R_c, R_d, R_e, R_f, R_g and R_h in structure B is hydrogen.

10. The method of claim 8, wherein the rinse contains 15% by weight of acetic acid and wherein each of R_a, R_b, R_c, R_d, R_e, R_f, R_g and R_h in structure B is hydrogen.

11. The method of claim 8, wherein the rinse contains 20% by weight of acetic acid and wherein each of R_a, R_b, R_c, R_d, R_e, R_f, R_g and R_h in structure B is hydrogen.

12. The method of claim 8, wherein the rinse contains 25% by weight of acetic acid and wherein each of R_a, R_b, R_c, R_d, R_e, R_f, R_g and R_h in structure B is hydrogen.

13. The method of claim 8, wherein the rinse contains 30% by weight of acetic acid and wherein each of R_a, R_b, R_c, R_d, R_e, R_f, R_g and R_h in structure B is hydrogen.

14. The method of claim 8, wherein the rinse contains 35% by weight of acetic acid and wherein each of R_a, R_b, R_c, R_d, R_e, R_f, R_g and R_h in structure B is hydrogen.

15. The method of claim 8, further comprising one or more steps selected from the group of:

(a) applying a masking agent on an edge and at least one proximate surface of the wafer or substrate;

(b) heating the applied masking agent to form the edge protection layer on the edge and at least one proximate surface of the wafer or substrate;

(c) applying a hardmask composition to the wafer or substrate and the edge protection layer;

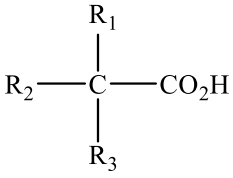
(d) removing at least a portion of the applied hardmask composition that is in contact with the edge protection layer, wherein the removing comprises rinsing the hardmask composition with at least one edge bead remover material;

(e) heating the applied hardmask composition to form the hardmask; and

(f) performing at least one post applied bake.

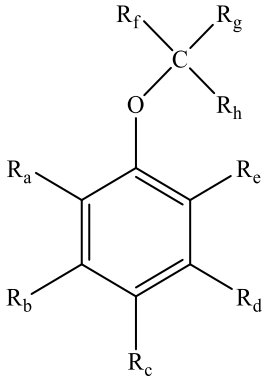
16. A rinse comprising

(i) between 1% by weight and 10% by weight of halogenated acetic acid of structure A:



wherein R_1 and R_2 are independently hydrogen or a halogen and R_3 is a halogen; and

(ii) between 99% by weight and 90% by weight of a compound having structure B:



wherein each of R_a, R_b, R_c, R_d, R_e, R_f, R_g and R_h may independently be hydrogen, a substituted or an unsubstituted (C_{1-6}) alkyl group, a substituted or an unsubstituted halogenated (C_{1-6}) alkyl group, a substituted or an unsubstituted (C_{1-6}) alkyl carbonyl group, a halogen, or a hydroxy group.

17. The rinse of claim 16, wherein each of R_a, R_b, R_c, R_d, R_e, R_f, R_g and R_h in structure B is hydrogen.

18. The rinse of claim 16, wherein in the halogenated acetic acid of structure A R_1 and R_2 are each hydrogen and R_3 is a halogen selected from among fluorine, bromine, iodine and chlorine

19. The rinse of claim 16, wherein in the halogenated acetic acid of structure A two or more of R_1, R_2 and R_3 is a halogen selected from among fluorine, bromine, iodine and chlorine.

20. The rinse of claim 16, wherein the halogenated acetic acid of structure A is difluoroacetic acid and wherein each of R_a, R_b, R_c, R_d, R_e, R_f, R_g and R_h in structure B is hydrogen.

21. The rinse of claim 16, wherein the halogenated acetic acid of structure A is trifluoroacetic acid and wherein each of R_a, R_b, R_c, R_d, R_e, R_f, R_g and R_h in structure B is hydrogen.

22. A method of cleaning a wafer or substrate comprising:

washing the wafer or substrate with a rinse according to claim 16.

23. The method of claim 22, further comprising one or more steps selected from the group of:

(a) applying a masking agent on an edge and at least one proximate surface of the wafer or substrate;

(b) heating the applied masking agent to form the edge protection layer on the edge and at least one proximate surface of the wafer or substrate;

(c) applying a hardmask composition to the wafer or substrate and the edge protection layer;

(d) removing at least a portion of the applied hardmask composition that is in contact with the edge protection layer, wherein the removing comprises rinsing the hardmask composition with at least one edge bead remover material;

(e) heating the applied hardmask composition to form the hardmask; and

(f) performing at least one post applied bake.